MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Advance Information

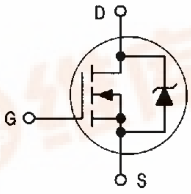
TMOS E-FET ™
Power Field Effect Transistor
N-Channel Enhancement-Mode Silicon Gate

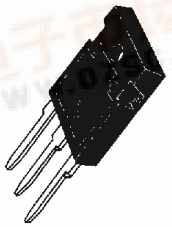
MTW6N60E
Motorola Preferred Device

TMOS POWER FET
6.0 AMPERES
$R_{DS(on)}$ = 1.20 OHM
600 VOLTS

This advanced TMOS E-FET is designed to withstand high energy in the avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional safety margin against unexpected voltage transients.

- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temeprature





CASE 340F-03
TO-247AE

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	600	Vdc
Drain-Gate Voltage (R_{GS} = 1 0 MΩ)	V_{DGR}	600	Vdc
Gate-Source Voltage — Continuous	V_{GS}	±20	Vdc
Drain Current — Continuous @ T_C = 25°C — Continuous @ T_C = 100°C — Single Pulse ($t_p \le 10$ µs)	I_D I_D I_{DM}	6 0 5 0 25	Adc Apk
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	150 1 0	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy — Starting T_J = 25°C (V_{DD} = 50 Vdc, V_{GS} = 10 Vpk, I_L = 6 0 Apk, L = 10 4 mH, R_G = 25 Ω)	E_{AS}	187	mJ
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.0 40	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 5 seconds	T_L	260	°C

This document contains information on a new product Specifications and information are subject to change without notice

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Preferred devices are Motorola recommended choices for future use and best overall value

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0 V, I_D = 250 µAdc)	BV_{DSS}	600	—	—	Vdc
Temperature Coefficient (Positive)		—	360	—	mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 600 Vdc, V_{GS} = 0)	I_{DSS}	—	—	250	µAdc
(V_{DS} = 600 Vdc, V_{GS} = 0, T_J = 125°C)		—	—	1000	
Gate-Body Leakage Current (V_{GS} = ±20 Vdc, V_{DS} = 0)	I_{GSS}	—	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 µAdc)	$V_{GS(th)}$	2.0	—	4 0	Vdc
Temperature Coefficient (Negative)		—	5.0	—	mV/°C
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 5.0 Adc)	$R_{DS(on)}$	—		1.2	Ohm
Drain-Source On-Voltage (V_{GS} = 10 Vdc) (I_D = 6.0 Adc)	$V_{DS(on)}$	—	—	8.0	Vpk
(I_D = 3.0 Adc, T_J = 125°C)		—	—	7.2	
Forward Transconductance (V_{DS} = 15 Vdc, I_D = 3.0 Adc)	g_{FS}	2.5	—	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{DS} = 25, Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	1435	—	pF
Output Capacitance	C_{oss}	—	175	—	
Reverse Transfer Capacitance	C_{rss}	—	35	—	
SWITCHING CHARACTERISTICS*†					
Turn-On Delay Time (V_{DD} = 300 Vdc, I_D = 6.0 Adc, V_{GS} = 10 Vdc, R_g = 9.1 Ω)	$t_{d(on)}$	—	22	50	ns
Rise Time	t_r	—	29	75	
Turn-Off Delay Time	$t_{d(off)}$	—	65	150	
Fall Time	t_f	—	34	65	
Gate Charge (V_{DS} = 420 Vdc, I_D = 6.0 Adc, V_{GS} = 10 Vdc)	Q_T	—	50	60	nC
	Q_1	—	8.0	—	
	Q_2	—	26	—	
	Q_3	—	30	—	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage (I_S = 6.0 Adc, V_{GS} = 0)	V_{SD}	—	1.3	1.5	Vdc
(I_S = 6.0 Adc, V_{GS} = 0, T_J = 125°C)		—	1.2	—	
Reverse Recovery Time (I_S = 6.0 Adc, V_{GS} = 0, dI_S/dt = 100 A/µs)	t_{rr}	—	330	—	ns
	t_a	—	220	—	
	t_b	—	110	—	
Reverse Recovery Stored Charge	Q_{RR}	—	4.3	—	µC
INTERNAL PACKAGE INDUCTANCE					
Internal Drain Inductance (Measured from the drain lead 0.25″ from package to center of die)	L_D	—	5.0	—	nH
Internal Source Inductance (Measured from the source lead 0.25″ from package to source bond pad)	L_S	—	13	—	nH

*Pulse Test. Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%

† Switching characteristics are independent of operating junction temperature